

BUK9Y22-30B

N-channel TrenchMOS logic level FET Rev. 04 — 7 April 2010

Product data sheet

Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$	-	-	30	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 4</u>	-	-	37.7	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	59.4	W
Static char	acteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 20 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 12}}{\text{see } \frac{\text{Figure 13}}{\text{Figure 13}}}$	-	17	22	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A};$ $T_j = 25 \text{ °C}$	-	13.5	19	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 37.7 \text{ A; } V_{sup} \leq 30 \text{ V;} \\ R_{GS} &= 50 \Omega; V_{GS} = 5 \text{ V;} \\ T_{j(init)} &= 25 ^{\circ}\text{C; } unclamped \end{split}$	-	-	47	mJ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 20 \text{ A};$ $V_{DS} = 24 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{ Figure } 14}$	-	4.5	-	nC

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb (D D
3	S	source		
4	G	gate	Q	G (F)
mb	D	mounting base; connected to drain	1 2 3 4	mb/798 S1 S2 S3
			SOT669 (LFPAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9Y22-30B	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

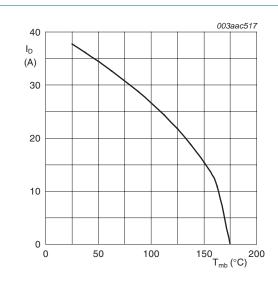
	_						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	-	30	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	30	V
V _{GS}	gate-source voltage			-15	-	15	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 5 V; see <u>Figure 1</u> ; see <u>Figure 4</u>		-	-	37.7	Α
		$T_{mb} = 100 ^{\circ}\text{C}; V_{GS} = 5 \text{V}; \text{see} \frac{\text{Figure 1}}{}$		-	-	26.65	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; $t_p \le 10 \mu s$; pulsed; see Figure 4		-	-	150.7	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	59.4	W
T _{stg}	storage temperature			-55	-	175	°C
T _j	junction temperature			-55	-	175	°C
Source-drain	diode						
Is	source current	T _{mb} = 25 °C		-	-	37.7	Α
I _{SM}	peak source current	$t_p \le 10 \mu s$; pulsed; $T_{mb} = 25 \text{ °C}$		-	-	150.7	Α
Avalanche rug	ggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 37.7 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω ; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	47	mJ
E _{DS(AL)R}	repetitive drain-source avalanche energy	see Figure 3	[1][2][3] [4]	-	-	-	J

^[1] Maximum value not quoted. Repetitive rating defined in avalanche rating figure.

^[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 $^{\circ}$ C.

^[3] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

^[4] Refer to application note AN10273 for further information.



Pder (%)

80

40 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$

Fig 1. Continuous drain current as a function of mounting base temperature

Fig 2. Normalized total power dissipation as a function of mounting base temperature

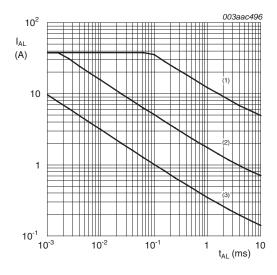
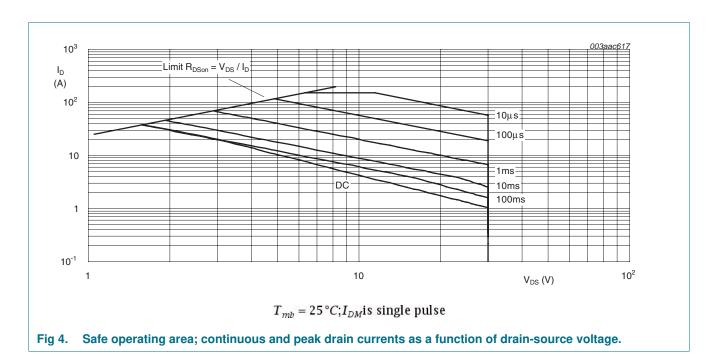


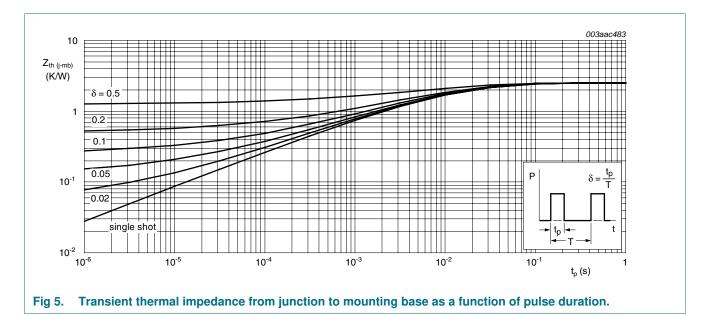
Fig 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	-	2.53	K/W



6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	27	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see <u>Figure 10</u> ; see <u>Figure 11</u>	1.1	1.5	2	V
	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	0.5	-	-	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	-	2.3	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I_{GSS}	gate leakage current	V _{DS} = 0 V; V _{GS} = 15 V; T _j = 25 °C	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -15 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon} drain-source on-s resistance	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 20 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	17	22	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C}$	-	-	24	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 20 \text{ A}; T_j = 175 °C;$ see Figure 12	-	-	44	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_i = 25 \text{ °C}$	-	13.5	19	mΩ
Dynamic	characteristics	·				
Q _{G(tot)}	total gate charge	$I_D = 20 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 5 \text{ V};$	-	10.5	-	nC
Q _{GS}	gate-source charge	see Figure 14	-	3.3	-	nC
Q _{GD}	gate-drain charge		-	4.5	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	705	940	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 15</u>	-	188	226	pF
C _{rss}	reverse transfer capacitance		-	102	140	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 25 \text{ V}; R_L = 1.25 \Omega; V_{GS} = 5 \text{ V};$	-	8.7	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega$	-	18.5	-	ns
t _{d(off)}	turn-off delay time		-	42	-	ns
t _f	fall time		-	23	-	ns
Source-di	rain diode					
V_{SD}	source-drain voltage	$I_S = 10 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 16	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	30	-	ns
Q _r	recovered charge	$V_{DS} = 30 \text{ V}$	-	33	-	nC

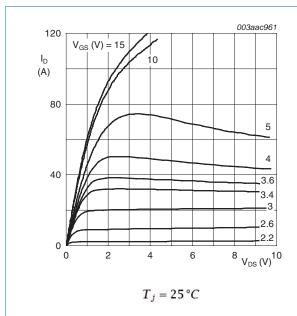


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values.

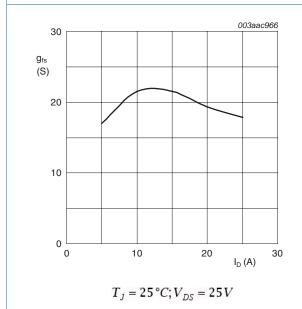
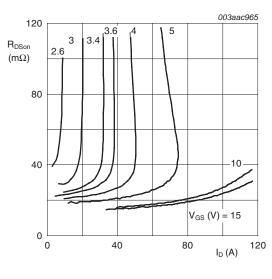
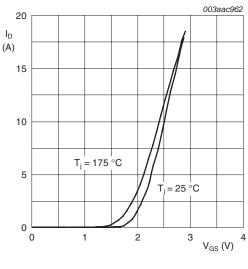


Fig 8. Forward transconductance as a function of drain current; typical values.



 $T_j=25\,^{\circ}C$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



 $V_{DS} = 25V$

Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values.

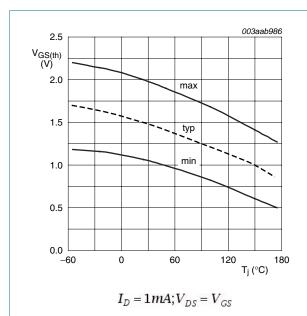


Fig 10. Gate-source threshold voltage as a function of junction temperature

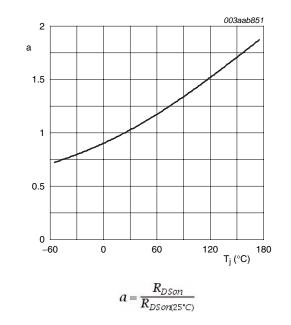
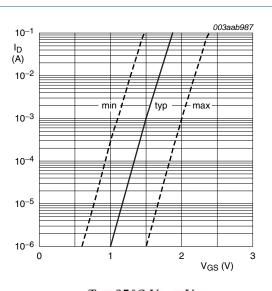
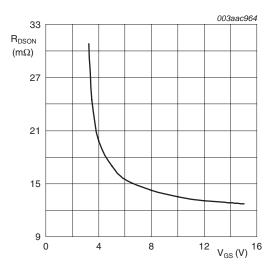


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



 $T_j=25\,^{\circ}C; V_{DS}=V_{GS}$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



 $T_j = 25 \,{}^{\circ}C; I_D = 20A$

Fig 13. Drain-source on-state resistance as a function of gate-source voltage; typical values.

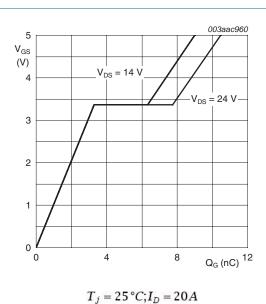
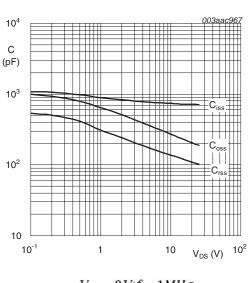


Fig 14. Gate-source voltage as a function of gate charge; typical values.



 $V_{GS} = 0V; f = 1MHz$

Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.

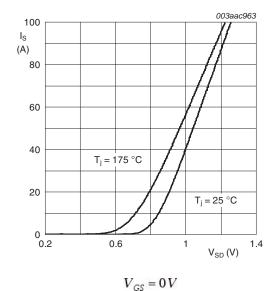


Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.

Package outline

Plastic single-ended surface-mounted package (LFPAK); 4 leads **SOT669** С c₂- E_1 mounting b₄ base D_1 D Х **→** w M A е 1/2 e (A_3) С detail X 5 mm scale **DIMENSIONS (mm are the original dimensions)** D₁⁽¹⁾ A₂ D⁽¹⁾ E⁽¹⁾ UNIT Α b b_2 b_4 E₁⁽¹⁾ L L_2 θ Α₁ A₃ b₃ С c_2 е L_1 у 1.20 0.15 1.10 0.50 4.41 0.9 0.25 0.30 4.10 3.3 6.2 0.85 1.3 1.27 0.25 0.00 0.95 0.35 3.62 2.0 0.7 0.19 0.24 0.40 8.0 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included. REFERENCES **EUROPEAN** OUTLINE **ISSUE DATE PROJECTION** VERSION IEC JEDEC

Fig 17. Package outline SOT669 (LFPAK)

BUK9Y22-30B

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JEITA

MO-235

04-10-13

06-03-16

SOT669

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9Y22-30B_4	20100407	Product data sheet	-	BUK9Y22-30B_3
Modifications:	 Status char 	nged from objective to pro	oduct.	
BUK9Y22-30B_3	20100216	Objective data sheet	-	BUK9Y22-30B_2

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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N-channel TrenchMOS logic level FET

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